FORM PTO-1449	Docket Number (Optional) 81790.0311	Application Number 10/768,238 Not assigned
INFORMATION DISCLOSURE CITATION IN AN APPLICATION *(Use several sheets if necessary)*	Applicant YAEGASHI et al.	
	Filing Date January 29, 2004	Group Art Unit 2815 Not assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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Q M	HANNON, et al., "0.25 µm Merged Bulk DRAM and SOI Logic Using Patterned SOI", 2000 Symposium on VLSI Technology Digest of Technical Papers pages, 66 - 67 ✗
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✗ No month cited.

EXAMINER Q M	DATE CONSIDERED 4/29/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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